

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Original) A purging method of a CVD apparatus that supplies semiconductor material gas to a reaction chamber in which a wafer is placed to form a semiconductor film on said wafer; wherein, a gas, comprising a mixture of a gas such as hydrogen or helium having a high coefficient of thermal conductivity and an inert gas, is used as the purge gas used during heated flow purging treatment.
3. (Currently amended) A purging method of a CVD apparatus that supplies semiconductor material gas to a reaction chamber in which a wafer is placed to form a semiconductor film on said wafer; according to claim 2, wherein, prior to semiconductor film formation after placing the wafer in the reaction chamber, the pumping of a vacuum inside the reaction chamber and the introduction of inert gas are repeated a plurality of times.
4. (Original) A method for judging the maintenance times of semiconductor production apparatuses that perform corrosive gas treatment in a reaction chamber by measuring the moisture concentration in the reaction chamber with a moisture meter connected to said reaction chamber when performing said corrosive gas treatment, and determining said maintenance times according to changes in said moisture concentration when corrosive gas treatment is performed repeatedly.
5. (Original) A method for judging the maintenance times of semiconductor production apparatuses according to claim 4 that determines said maintenance times according to the cumulative amount of moisture by calculating the cumulative amount of moisture that has accumulated from the previous round of maintenance and been taken into said reaction chamber based on said change in moisture concentration.

6. (Original) A method for judging the maintenance times of semiconductor production apparatuses according to claim 5 comprising measuring the pressure inside a reaction chamber with a pressure gauge connected to said reaction chamber when performing said corrosive gas treatment, and determining said maintenance times according to said cumulative amount of moisture and the change in said pressure when corrosive gas treatment is performed repeatedly.

7. (Original) A method for judging the maintenance times of semiconductor production apparatuses according to claim 4 wherein said moisture meter is a laser moisture meter that directs laser light into a tubular cell body connected to said reaction chamber and measures the absorption spectrum of the transmitted laser light.